

30V, 190A, 2.8mΩ N-channel Power Trench MOSFET

JMTC018N03A

Features

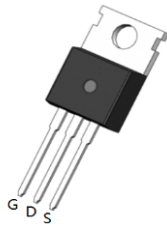
- Excellent $R_{DS(ON)}$ and Low Gate Charge
- 100% UIS Tested
- 100% ΔV_{ds} Tested
- Halogen-free; RoHS-compliant

Applications

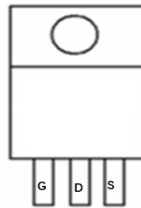
- Load Switch
- PWM Application
- Power Management

Product Summary

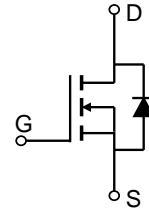
Parameters	Value	Unit
V_{DSS}	30	V
$V_{GS(th_Typ)}$	1.5	V
$I_D(@V_{GS}=10V)$	190	A
$R_{DS(ON_Typ)}(@V_{GS}=10V)$	2.2	mΩ
$R_{DS(ON_Typ)}(@V_{GS}=4.5V)$	2.8	mΩ



TO-220-3L



Pin Assignment



Schematic Diagram

Ordering Information

Device	Marking	MSL	Form	Package	Reel(pcs)	Per Carton (pcs)
JMTC018N03A	JMTC018N03A	NA	Tape&Reel	TO-220-3L	50	5000

Absolute Maximum Ratings (@ $T_C = 25^\circ\text{C}$ unless otherwise specified)

Symbol	Parameter	Value	Unit
V_{DS}	Drain-to-Source Voltage	30	V
V_{GS}	Gate-to-Source Voltage	± 20	V
I_D	Continuous Drain Current	$T_C = 25^\circ\text{C}$	190
		$T_C = 100^\circ\text{C}$	120
I_{DM}	Pulsed Drain Current ⁽¹⁾	Refer to Fig.4	A
E_{AS}	Single Pulsed Avalanche Energy ⁽²⁾	271	mJ
P_D	Power Dissipation	$T_C = 25^\circ\text{C}$	138.9
		$T_C = 100^\circ\text{C}$	55.6
T_J, T_{STG}	Junction & Storage Temperature Range	-55 to 150	$^\circ\text{C}$

Thermal Characteristics

Symbol	Parameter	Max	Unit
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient ⁽³⁾	35	$^\circ\text{C/W}$
$R_{\theta JC}$	Thermal Resistance, Junction to Case	0.9	

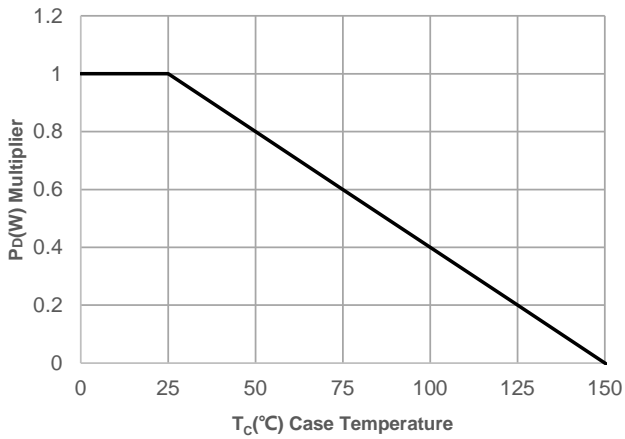
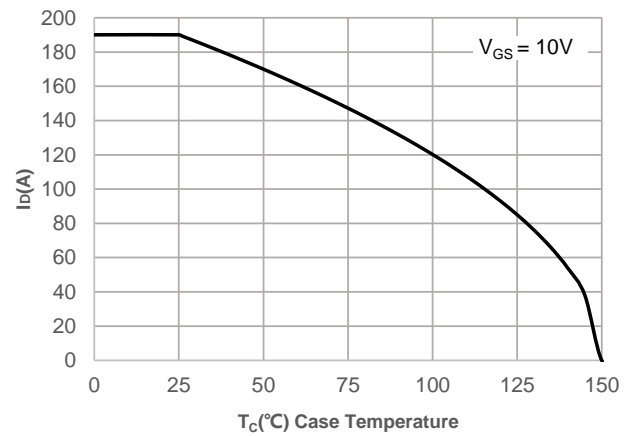
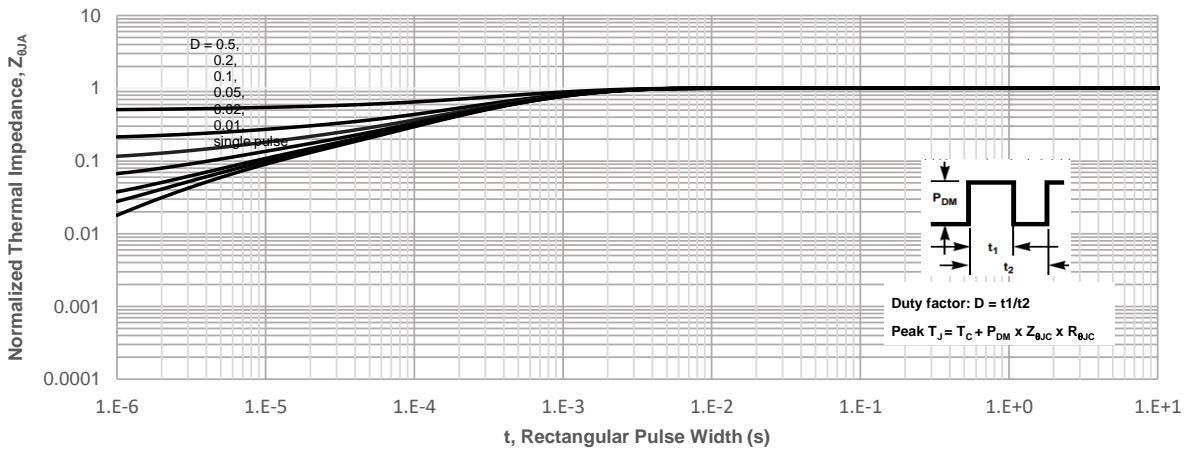
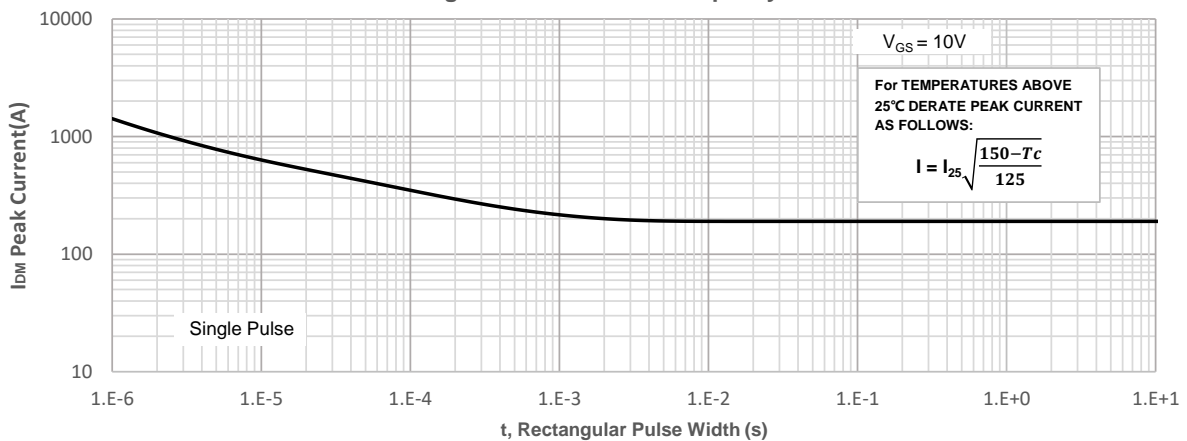
**Electrical Characteristics** ($T_J = 25^\circ\text{C}$ unless otherwise specified)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
Off Characteristics						
$V_{(BR)DSS}$	Drain-Source Breakdown Voltage	$I_D = 250\mu\text{A}$, $V_{GS} = 0\text{V}$	30	-	-	V
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS} = 30\text{V}$, $V_{GS} = 0\text{V}$	-	-	1.0	μA
I_{GSS}	Gate-Body Leakage Current	$V_{DS} = 0\text{V}$, $V_{GS} = \pm 20\text{V}$	-	-	± 100	nA
On Characteristics						
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS} = V_{GS}$, $I_D = 250\mu\text{A}$	1.1	1.5	2.5	V
$R_{DS(ON)}$	Static Drain-Source ON-Resistance ⁽⁴⁾	$V_{GS} = 10\text{V}$, $I_D = 30\text{A}$	-	2.2	2.7	$\text{m}\Omega$
		$V_{GS} = 4.5\text{V}$, $I_D = 20\text{A}$	-	2.8	4.2	$\text{m}\Omega$
Dynamic Characteristics						
R_g	Gate Resistance	$f = 1\text{MHz}$	-	2.1	-	Ω
C_{iss}	Input Capacitance	$V_{GS} = 0\text{V}$, $V_{DS} = 15\text{V}$, $f = 1\text{MHz}$	4484	6278	8475	pF
C_{oss}	Output Capacitance		616	863	1164	pF
C_{rss}	Reverse Transfer Capacitance		380	532	718	pF
Q_g	Total Gate Charge	$V_{GS} = 0$ to 10V $V_{DS} = 15\text{V}$, $I_D = 30\text{A}$	77	108	146	nC
Q_{gs}	Gate Source Charge		14	20	27	nC
Q_{gd}	Gate Drain ("Miller") Charge		14	20	27	nC
Switching Characteristics						
$t_{d(on)}$	Turn-On Delay Time	$V_{GS} = 10\text{V}$, $V_{DD} = 15\text{V}$ $I_D = 30\text{A}$, $R_{GEN} = 3\Omega$	-	13	-	ns
t_r	Turn-On Rise Time		-	29	-	ns
$t_{d(off)}$	Turn-Off Delay Time		-	85	-	ns
t_f	Turn-Off Fall Time		-	50	-	ns
Body Diode Characteristics						
I_S	Maximum Continuous Body Diode Forward Current		-	-	190	A
I_{SM}	Maximum Pulsed Body Diode Forward Current		-	-	760	A
V_{SD}	Body Diode Forward Voltage	$V_{GS} = 0\text{V}$, $I_S = 30\text{A}$	-		1.2	V
t_{rr}	Body Diode Reverse Recovery Time	$I_F = 20\text{A}$, $di/dt = 100\text{A}/\mu\text{s}$	20	28	38	ns
Q_{rr}	Body Diode Reverse Recovery Charge		-	16.0	-	nC

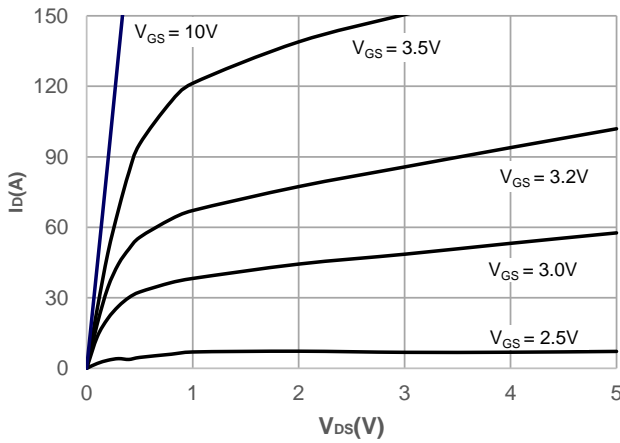
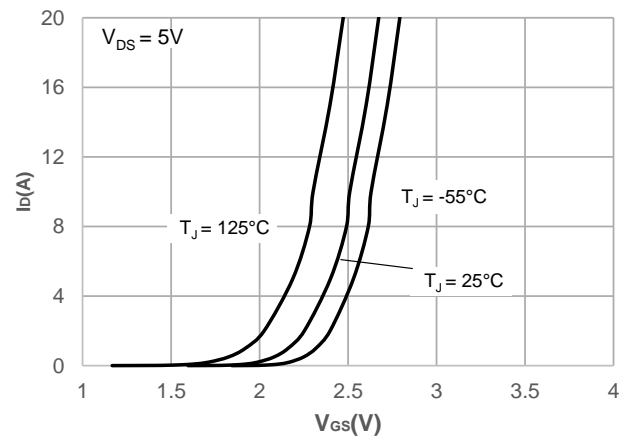
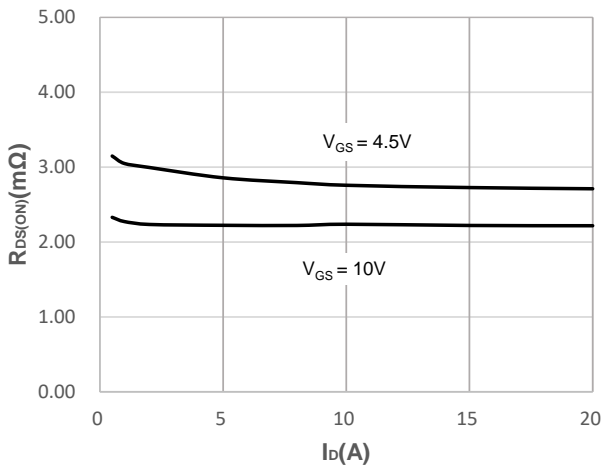
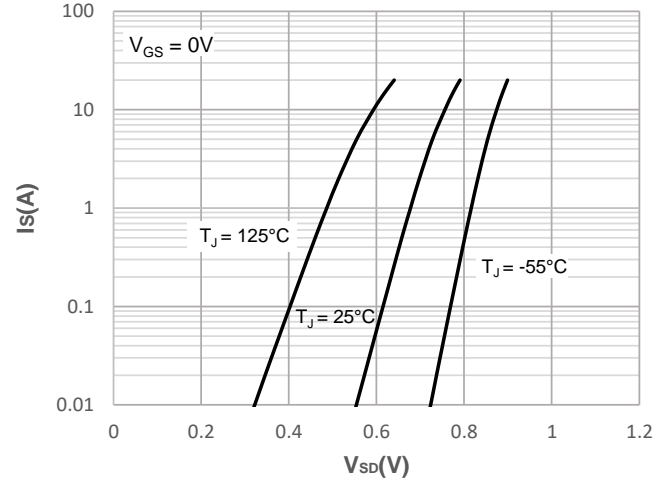
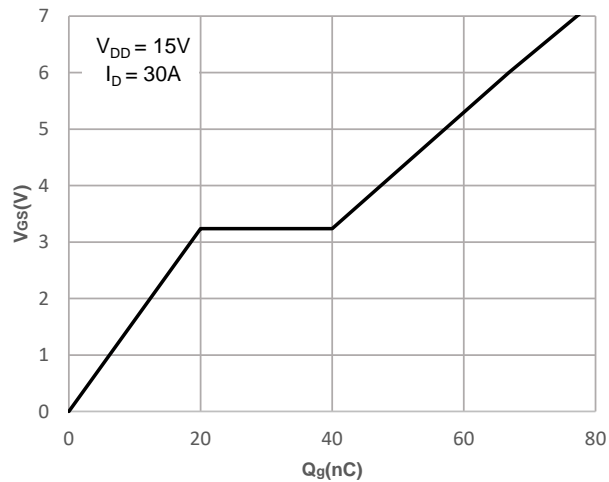
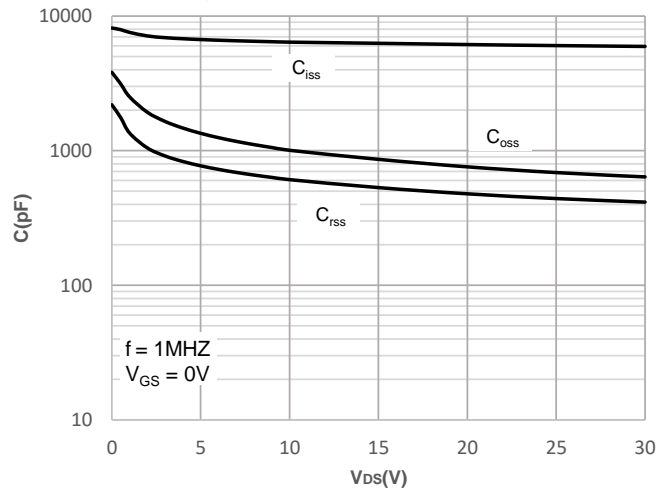
- Notes:
1. Repetitive Rating: Pulse Width Limited by Maximum Junction Temperature.
 2. E_{AS} condition: Starting $T_J = 25^\circ\text{C}$, $V_{DD} = 15\text{V}$, $V_G = 10\text{V}$, $R_G = 25\text{ohm}$, $L = 0.5\text{mH}$, $I_{AS} = 33.04\text{A}$, $V_{DD} = 0\text{V}$ during time in avalanche.
 3. $R_{\theta JA}$ is measured with the device mounted on a 1inch^2 pad of 2oz copper FR4 PCB.
 4. Pulse Test: Pulse Width $\leq 300\mu\text{s}$, Duty Cycle $\leq 0.5\%$.



Typical Performance Characteristics

Figure 1: Power De-rating

Figure 2: Current De-rating

Figure 3: Normalized Maximum Transient Thermal Impedance

Figure 4: Peak Current Capacity


Typical Performance Characteristics

Figure 5: Output Characteristics

Figure 6: Typical Transfer Characteristics

Figure 7: On-resistance vs. Drain Current

Figure 8: Body Diode Characteristics

Figure 9: Gate Charge Characteristics

Figure 10: Capacitance Characteristics


Typical Performance Characteristics

Figure 11: Normalized Breakdown voltage vs. Junction Temperature

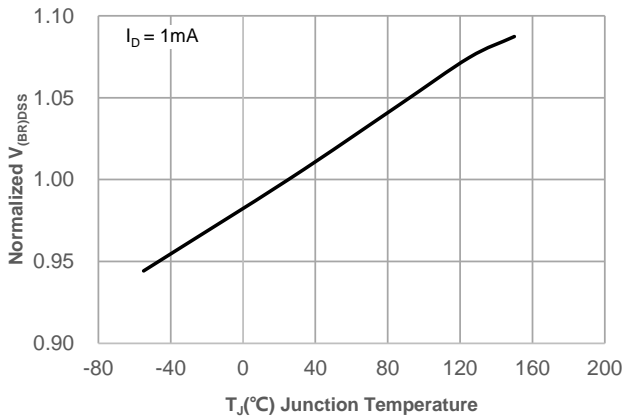


Figure 12: Normalized on Resistance vs. Junction Temperature

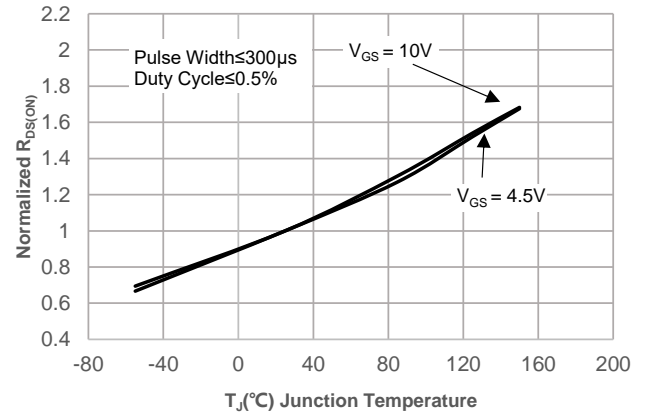


Figure 13: Normalized Threshold Voltage vs. Junction Temperature

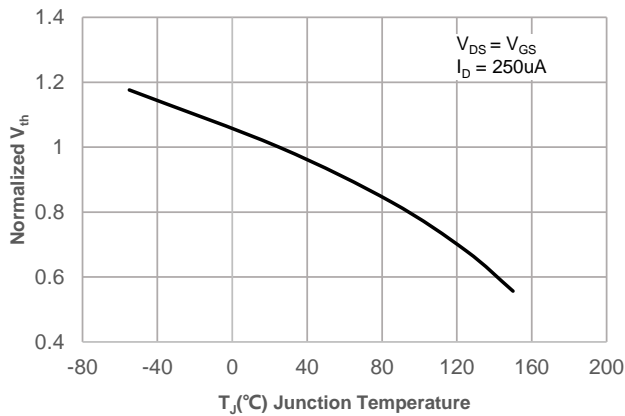


Figure 14: $R_{DS(ON)}$ vs. V_{GS}

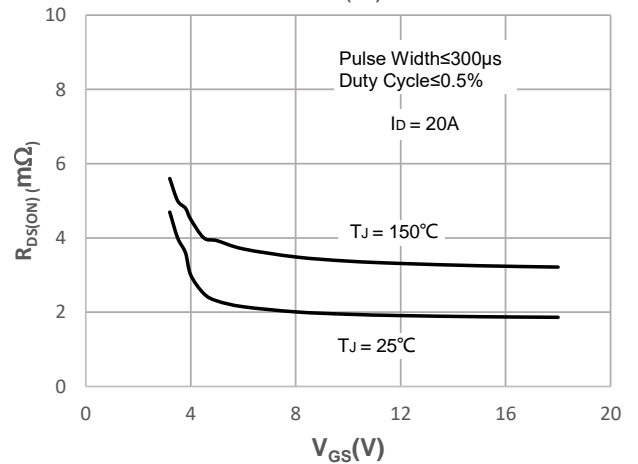
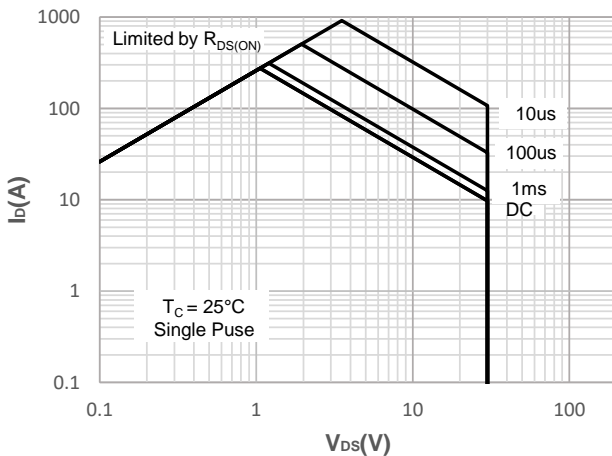
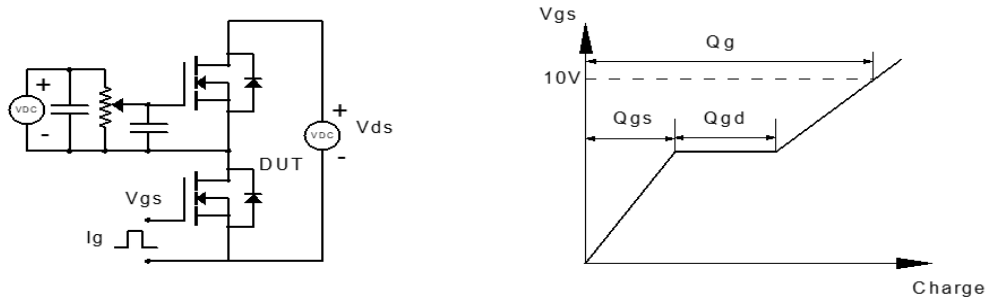
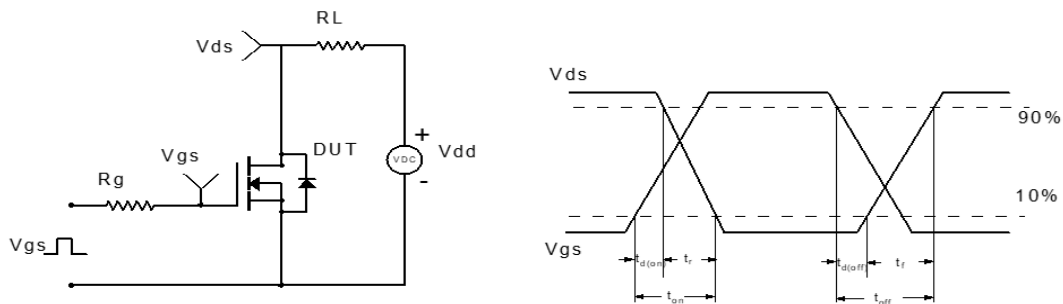
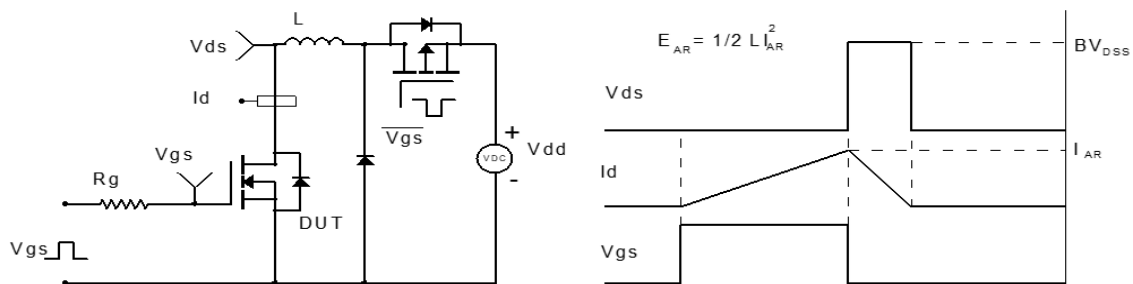
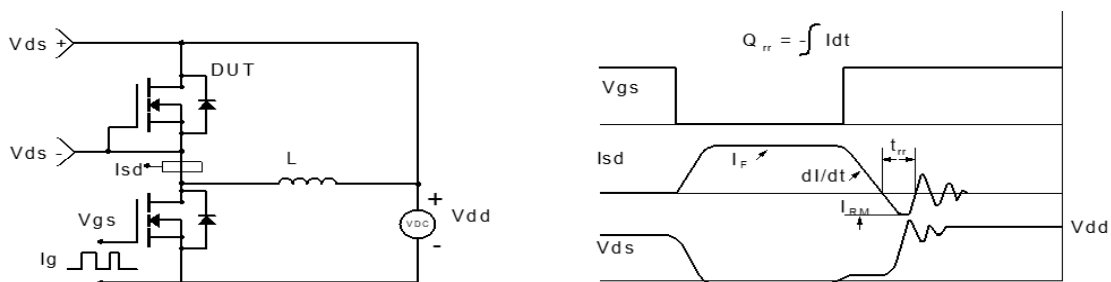
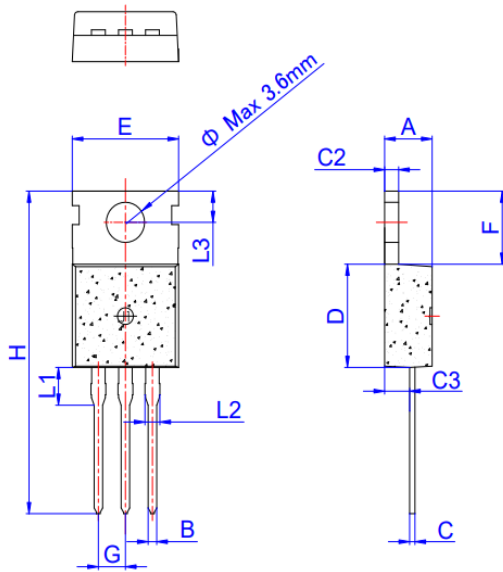


Figure 15: Maximum Safe Operating Area



Test Circuit

Figure 1: Gate Charge Test Circuit & Waveform

Figure 2: Resistive Switching Test Circuit & Waveform

Figure 3: Unclamped Inductive Switching Test Circuit & Waveform

Figure 4: Diode Recovery Test Circuit & Waveform


Package Mechanical Data(TO-220-3L)


TO-220C

Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	4.40		4.60	0.173		0.181
B	0.70		0.90	0.028		0.035
C	0.45		0.60	0.018		0.024
C2	1.23		1.32	0.048		0.052
C3	2.20		2.60	0.087		0.102
D	8.90		9.90	0.350		0.390
E	9.90		10.3	0.390		0.406
F	6.30		6.90	0.248		0.272
G		2.54			0.1	
H	28.0		29.8	1.102		1.173
L1		3.39			0.133	
L2	1.14		1.70	0.045		0.067
L3	2.65		2.95	0.104		0.116
Φ		3.6			0.142	

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